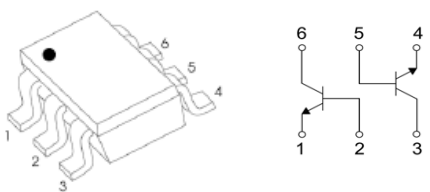
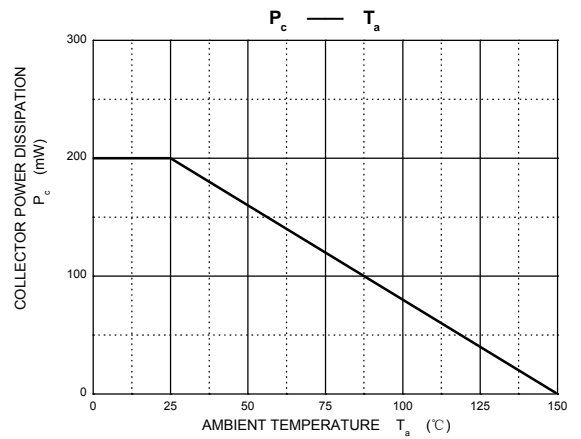
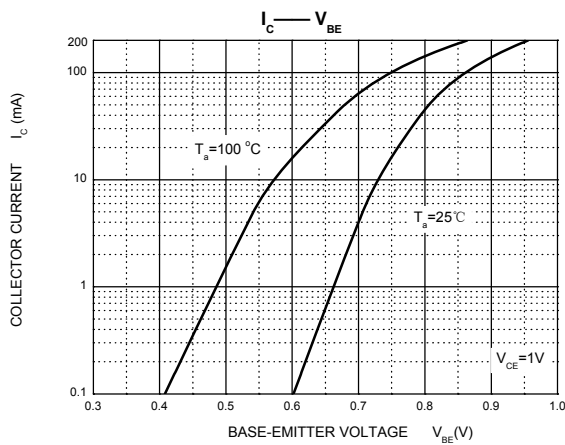
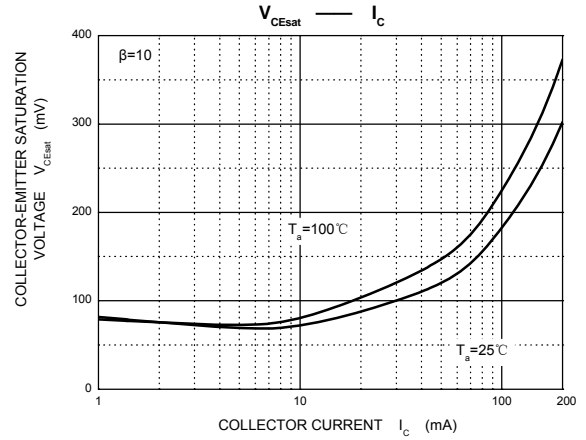
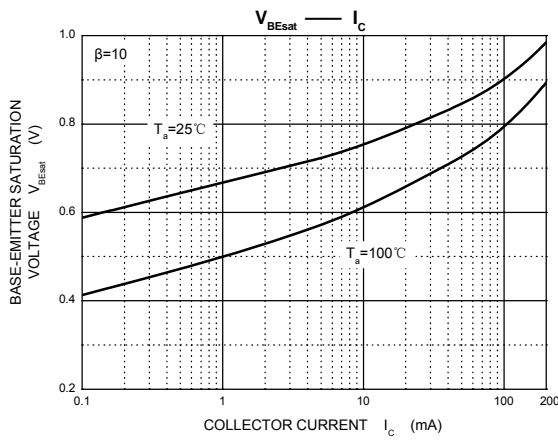
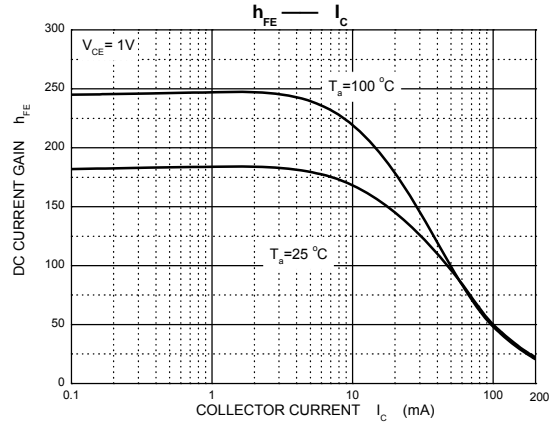
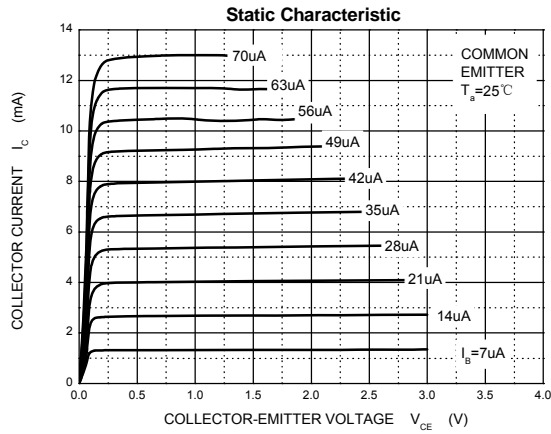


DUAL TRANSISTOR (NPN+NPN)		SOT-363 Plastic-Encapsulate Transistors				
<p style="text-align: center;"><u>SOT-363</u></p> 		Features <ul style="list-style-type: none"> • Epitaxial planar die construction • Ideal for low power amplification and switching 				
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)						
Symbol	Parameter	Value	Units			
V _{CB0}	Collector-Base Voltage	60	V			
V _{CEO}	Collector-Emitter Voltage	40	V			
V _{EBO}	Emitter-Base Voltage	5	V			
I _C	Collector Current -Continuous	0.2	A			
P _C	Collector Power Dissipation	0.2	W			
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C			
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)						
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			0.05	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.05	μA
Collector cut-off current	I _{CEX}	V _{CE} =30V, V _{BE(off)} =3V			0.05	μA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C =0.1mA	40			
	h _{FE(2)}	V _{CE} =1V, I _C =1mA	70			
	h _{FE(3)}	V _{CE} =1V, I _C =10mA	100		300	
	h _{FE(4)}	V _{CE} =1V, I _C =50mA	60			
	h _{FE(5)}	V _{CE} =1V, I _C =100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =10mA, I _B =1mA			0.2	V
	V _{CE(sat)2}	I _C =50mA, I _B =5mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =10mA, I _B =1mA	0.65		0.85	V
	V _{BE(sat)2}	I _C =50mA, I _B =5mA			0.95	V
Transition frequency	f _T	V _{CE} =20V, I _C =10mA, f=100MHz	300			MHz
Collector output capacitance	C _{ob}	V _{CB} =5V, I _E =0, f=1MHz			4	pF
Noise figure	NF	V _{CE} =5V, I _C =0.1mA, f=1kHz, R _S =1KΩ			5	dB
Delay time	t _d	V _{CC} =3V, V _{BE(off)} =-0.5V			35	nS
Rise time	t _r	I _C =10mA, I _{B1} =-I _{B2} =1mA			35	nS
Storage time	t _s	V _{CC} =3V, I _C =10mA			200	nS
Fall time	t _f	I _{B1} =-I _{B2} =1mA			50	nS

Typical Characteristics



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)